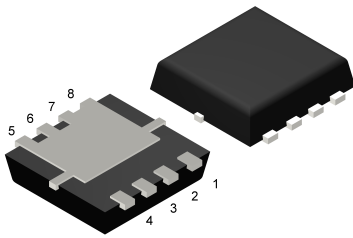
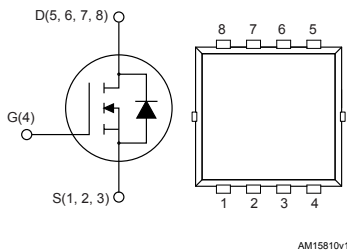


N-channel 100 V, 62 mΩ typ., 4.5 A STripFET™ F7 Power MOSFET in a PowerFLAT™ 3.3x3.3 package



PowerFLAT™ 3.3x3.3



Features

Order code	V _{DS}	R _{DS(on)} max.	I _D
STL4N10F7	100 V	70 mΩ	4.5 A

- Excellent FoM (figure of merit)
- Low C_{rss}/C_{iss} ratio for EMI immunity
- High avalanche ruggedness

Applications

- Switching applications

Description

This N-channel Power MOSFET utilizes STripFET™ F7 technology with an enhanced trench gate structure that results in very low on-state resistance, while also reducing internal capacitance and gate charge for faster and more efficient switching.

Maturity status link

[STL4N10F7](#)

Device summary

Order code	STL4N10F7
Marking	4N1F7
Package	PowerFLAT™ 3.3x3.3
Packing	Tape and reel

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	100	V
V_{GS}	Gate-source voltage	± 20	V
$I_D^{(1)}$	Drain current (continuous) at $T_{pcb} = 25\text{ }^\circ\text{C}$	4.5	A
	Drain current (continuous) at $T_{pcb} = 100\text{ }^\circ\text{C}$	3.2	A
$I_{DM}^{(1)(2)}$	Drain current (pulsed)	18	A
$P_{TOT}^{(1)}$	Total dissipation at $T_{pcb} = 25\text{ }^\circ\text{C}$	2.9	W
$I_D^{(3)}$	Drain current (continuous) at $T_c = 25\text{ }^\circ\text{C}$	17	A
	Drain current (continuous) at $T_c = 100\text{ }^\circ\text{C}$	11	A
$I_{DM}^{(2)(3)}$	Drain current (pulsed)	68	A
$P_{TOT}^{(3)}$	Total dissipation at $T_c = 25\text{ }^\circ\text{C}$	35.7	W
T_j	Operating junction temperature range	-55 to 150	$^\circ\text{C}$
T_{stg}	Storage temperature range		$^\circ\text{C}$

1. This value is rated according to $R_{thj-pcb}$.
2. Pulse width is limited by safe operating area.
3. This value is rated according to $R_{thj-case}$.

Table 2. Thermal resistance

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	3.5	$^\circ\text{C}/\text{W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb	42.8	$^\circ\text{C}/\text{W}$

1. When mounted on an 1-inch² FR-4 board, 2oz Cu, $t < 10\text{ s}$

2 Electrical characteristics

($T_C = 25\text{ °C}$ unless otherwise specified)

Table 3. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$	100			V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$, $V_{DS} = 100\text{ V}$			1	μA
		$V_{GS} = 0\text{ V}$, $V_{DS} = 100\text{ V}$, $T_C = 125\text{ °C}^{(1)}$			100	μA
I_{GSS}	Gate-body leakage current	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 20\text{ V}$			100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2.5		4.5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$, $I_D = 2.25\text{ A}$		62	70	m Ω

1. Defined by design, not subject to production test.

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 50\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0\text{ V}$	-	408	-	pF
C_{oss}	Output capacitance		-	112	-	pF
C_{riss}	Reverse transfer capacitance		-	10	-	pF
Q_g	Total gate charge	$V_{DD} = 50\text{ V}$, $I_D = 4.5\text{ A}$, $V_{GS} = 0\text{ to }10\text{ V}$ (see Figure 15. Test circuit for gate charge behavior)	-	7.8	-	nC
Q_{gs}	Gate-source charge		-	3	-	nC
Q_{gd}	Gate-drain charge		-	1.7	-	nC

Table 5. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 50\text{ V}$, $I_D = 2.25\text{ A}$, $R_G = 4.7\text{ }\Omega$, $V_{GS} = 10\text{ V}$	-	6.3	-	ns
t_r	Rise time		-	3	-	ns
$t_{d(off)}$	Turn-off delay time	(see Figure 14. Test circuit for resistive load switching times and Figure 19. Switching time waveform)	-	11	-	ns
t_f	Fall time		-	4	-	ns

Table 6. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{SD}^{(1)}$	Forward on voltage	$I_{SD} = 2.25\text{ A}$, $V_{GS} = 0\text{ V}$	-		1.1	V

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
t_{rr}	Reverse recovery time	$I_{SD} = 2.25\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 80\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ (see Figure 16. Test circuit for inductive load switching and diode recovery times)	-	30		ns
Q_{rr}	Reverse recovery charge		-	24		nC
I_{RRM}	Reverse recovery current		-	1.6		A

1. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 3. Safe operating area

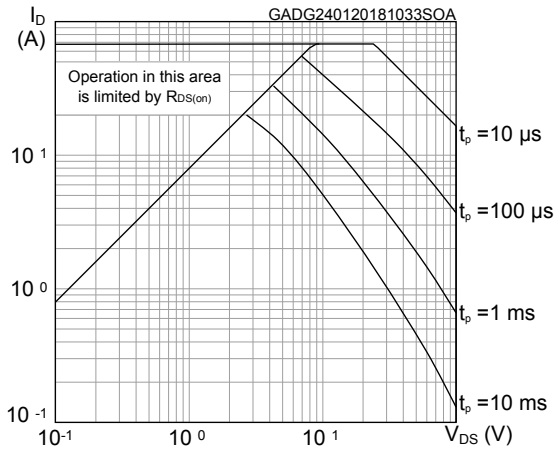


Figure 4. Thermal impedance

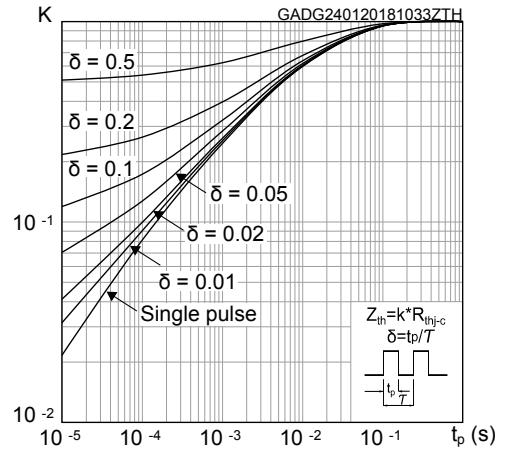


Figure 5. Output characteristics

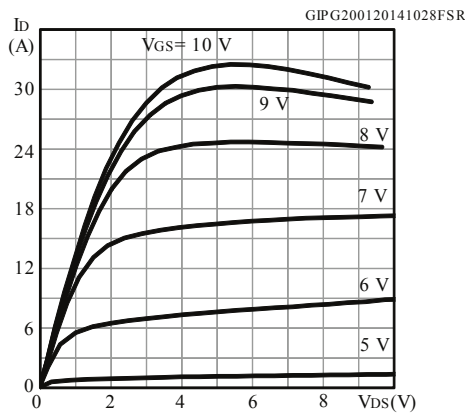


Figure 6. Transfer characteristics

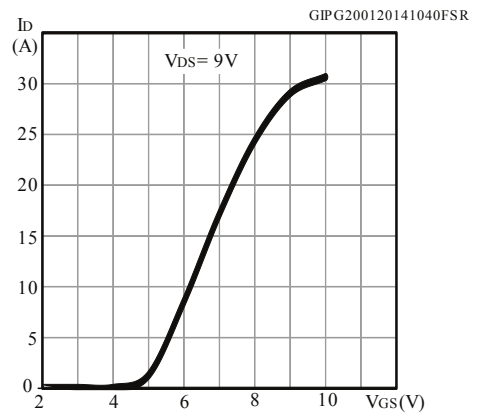


Figure 7. Gate charge vs gate-source voltage

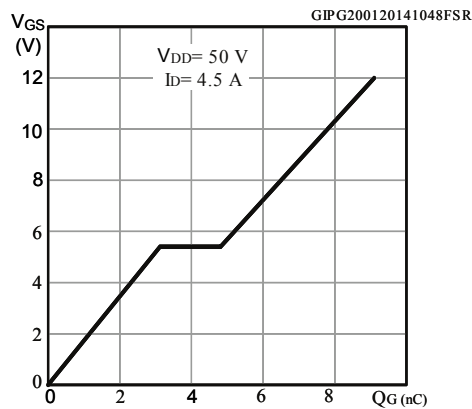


Figure 8. Static drain-source on-resistance

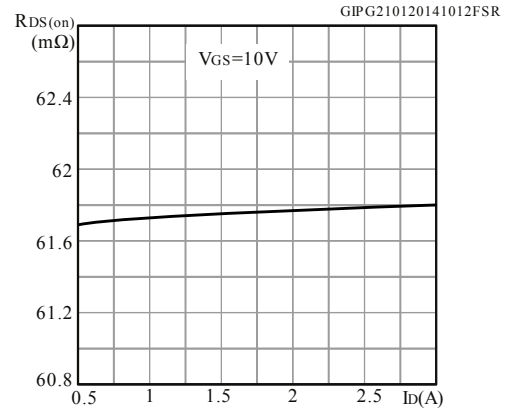
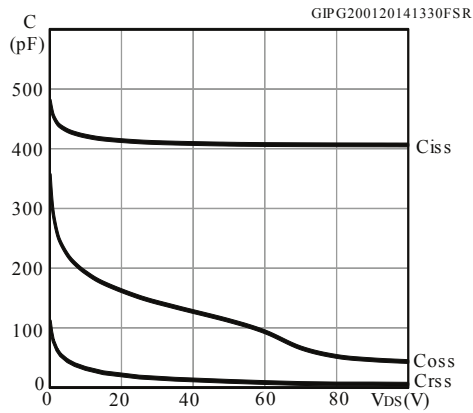
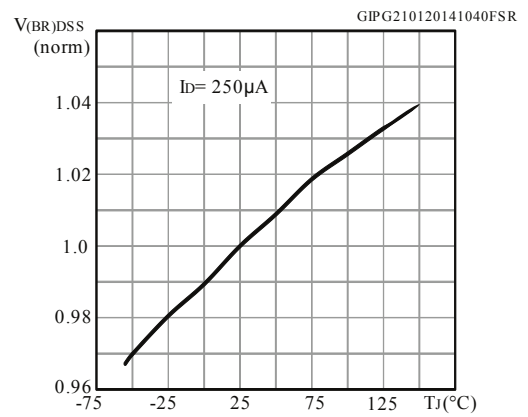
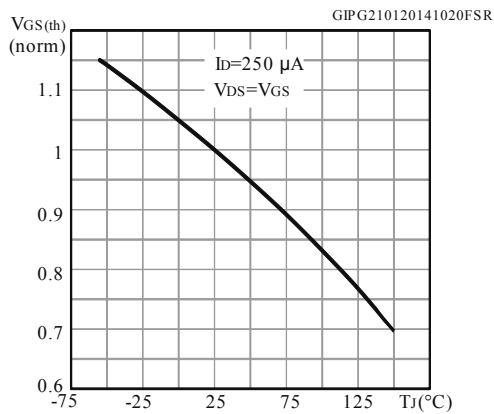
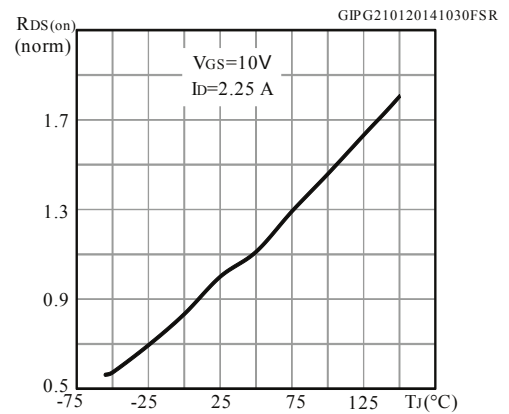
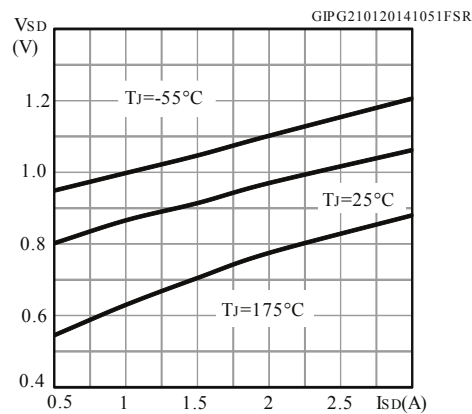
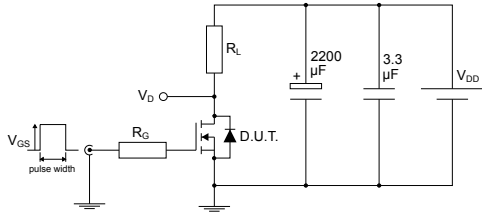
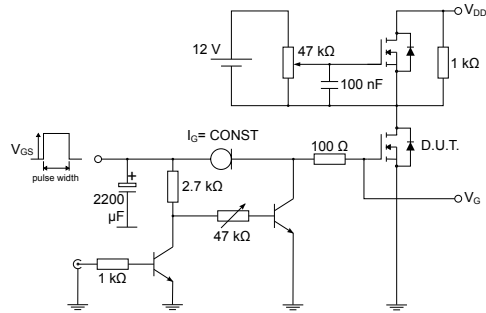


Figure 9. Capacitance variations

Figure 10. Normalized $V_{(BR)DSS}$ vs temperature

Figure 11. Normalized gate threshold voltage vs temperature

Figure 12. Normalized on-resistance vs temperature

Figure 13. Source-drain diode forward characteristics


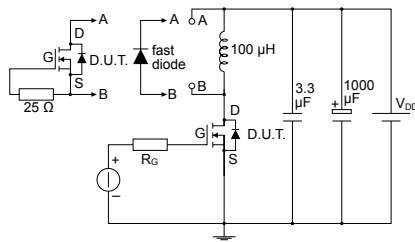
3 Test circuits

Figure 14. Test circuit for resistive load switching times


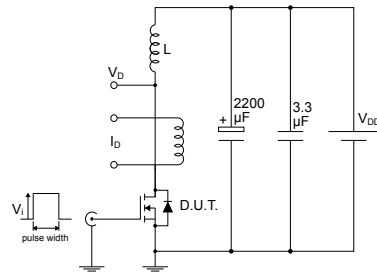
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Figure 15. Test circuit for gate charge behavior


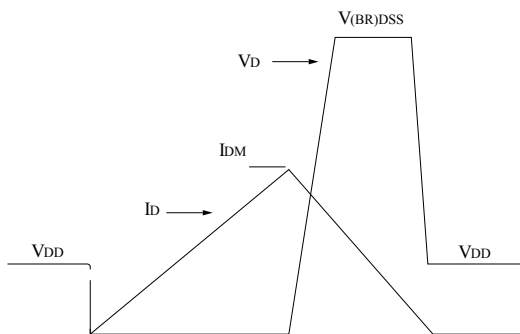
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Figure 16. Test circuit for inductive load switching and diode recovery times


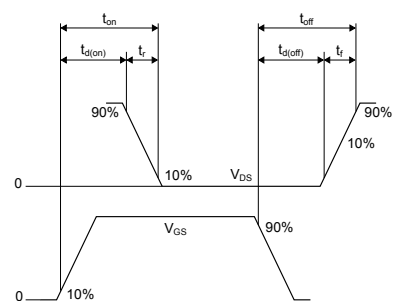
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Figure 17. Unclamped inductive load test circuit


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Figure 18. Unclamped inductive waveform


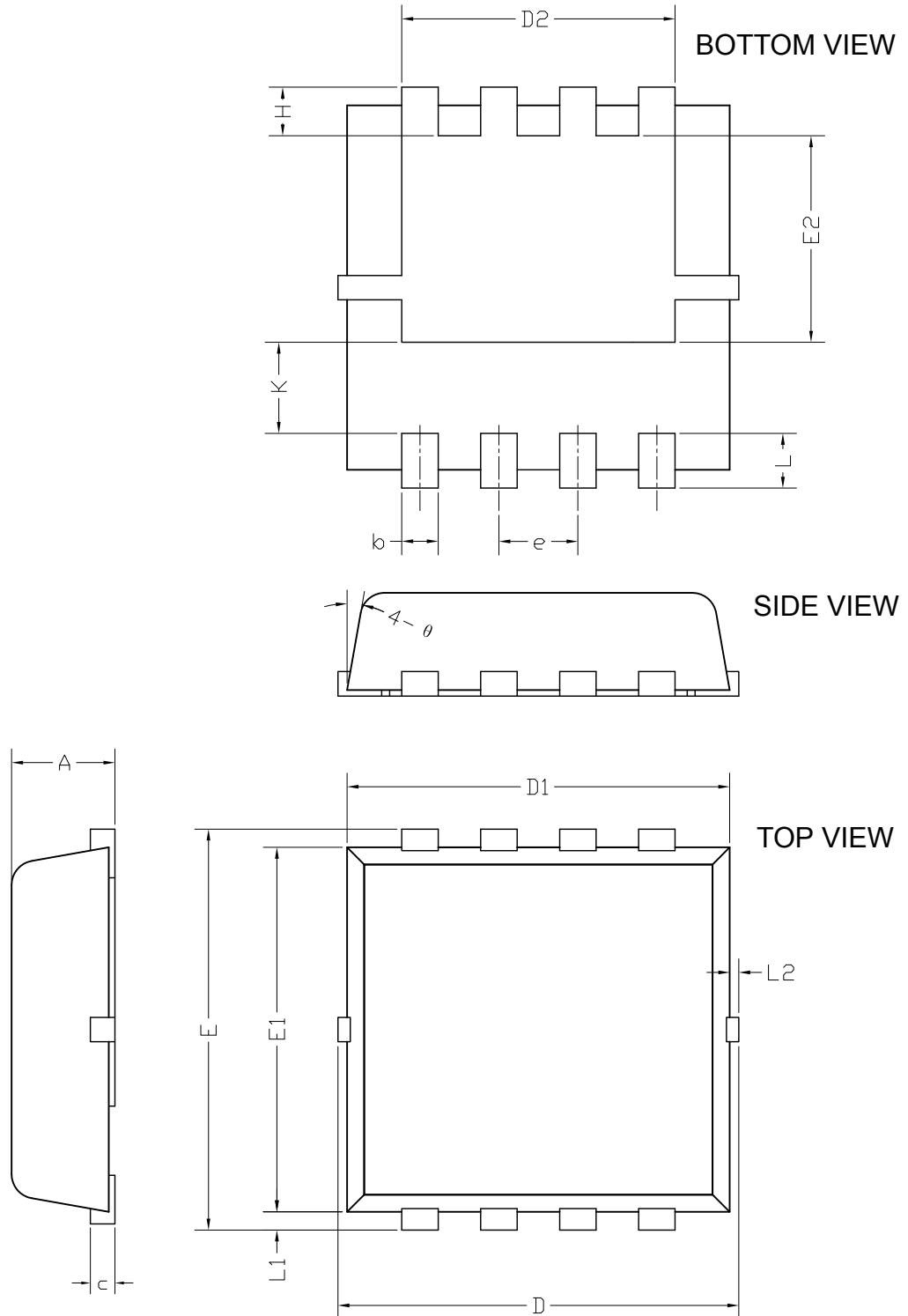
AM01472v1

Figure 19. Switching time waveform


AM01473v1

4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

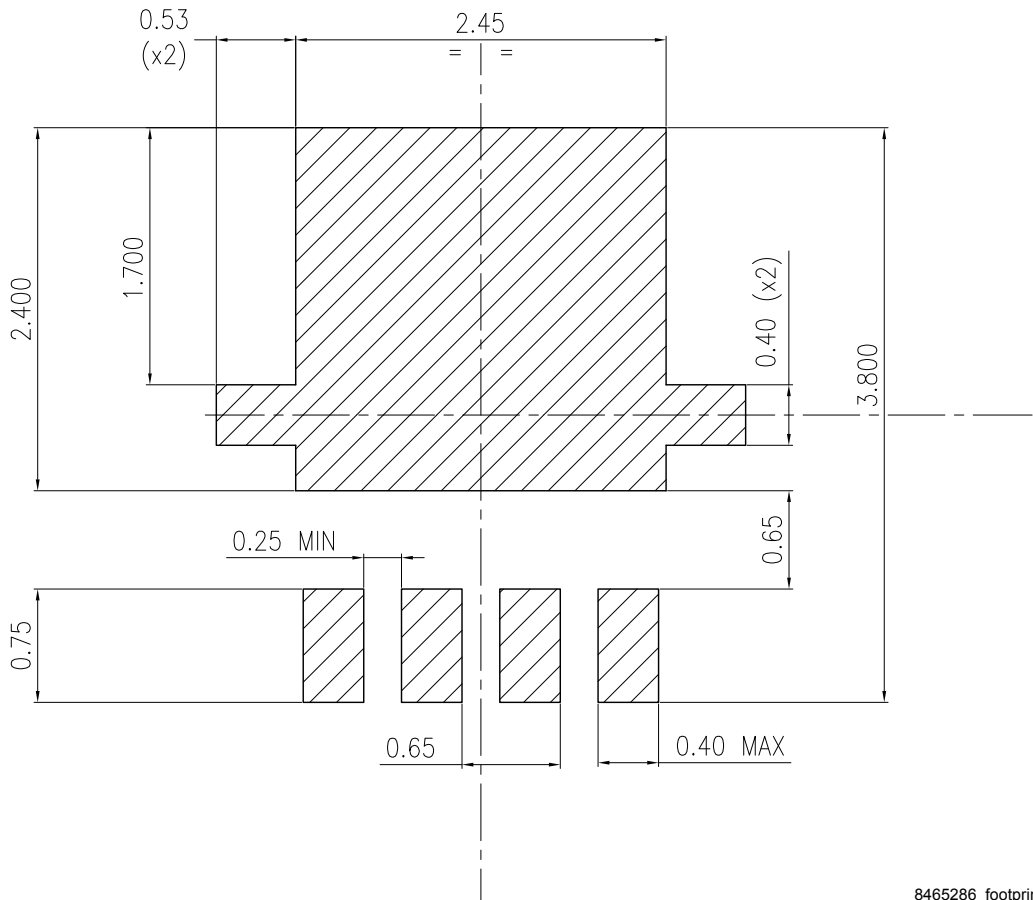
4.1 PowerFLAT™ 3.3x3.3 package information
Figure 20. PowerFLAT™ 3.3x3.3 package outline


8465286_2

Table 7. PowerFLAT™ 3.3x3.3 package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.70	0.80	0.90
b	0.25	0.30	0.39
c	0.14	0.15	0.20
D	3.10	3.30	3.50
D1	3.05	3.15	3.25
D2	2.15	2.25	2.35
e	0.55	0.65	0.75
E	3.10	3.30	3.50
E1	2.90	3.00	3.10
E2	1.60	1.70	1.80
H	0.25	0.40	0.55
K	0.65	0.75	0.85
L	0.30	0.45	0.60
L1	0.05	0.15	0.25
L2			0.15
θ	8°	10°	12°

Figure 21. PowerFLAT™ 3.3x3.3 recommended footprint (dimensions in mm)



8465286_footprint

Revision history

Table 8. Document revision history

Date	Revision	Changes
10-Jul-2013	1	First release.
21-Jan-2014	2	Inserted <i>Section 2.1: Electrical characteristics (curves)</i> . Document status promoted from preliminary to production data.
19-Feb-2014	3	Added: I_D (at $T_C = 25\text{ °C}$ and 125 °C), I_{DM} and P_{TOT} in <i>Table 2</i> Modified: <i>Figure 2</i> and <i>3</i> Minor text changes
10-Mar-2014	4	Modified: marking in <i>Table 1</i> Minor text changes
01-Feb-2018	5	Updated title, features and description on cover page. Removed maturity status indication from cover page. Updated Section 1 Electrical ratings . Updated Table 6. Source drain diode . Updated Section 2.1 Electrical characteristics (curves) . Minor text changes

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